

International
IR Rectifier

Plug N Drive™ Integrated Power
 Module for Appliance Motor Drive

IRAMS10UP60B

iMOTION™ Series

10A, 600V

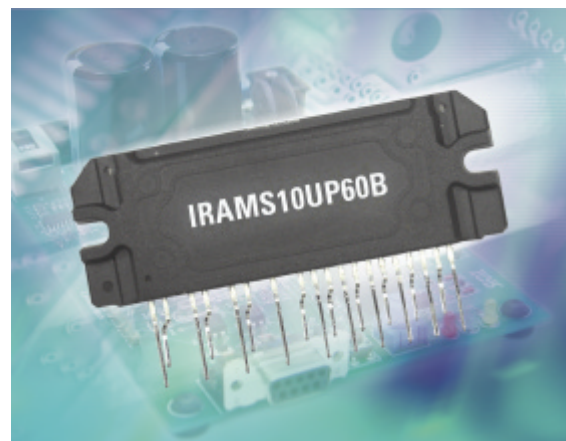
with Internal Shunt Resistor

Description

International Rectifier's IRAMS10UP60B is an Integrated Power Module developed and optimized for electronic motor control in appliance applications such as washing machines and refrigerators. Plug N Drive technology offers an extremely compact, high performance AC motor-driver in a single isolated package for a very simple design. An internal shunt is also included and offers easy current feedback and overcurrent monitor for precise and safe operation. A built-in temperature monitor and over-current protection, along with the short-circuit rated IGBTs and integrated under-voltage lockout function, deliver high level of protection and fail-safe operation. The integration of the bootstrap diodes for the high-side driver section, and the single polarity power supply required to drive the internal circuitry, simplify the utilization of the module and deliver further cost reduction advantages.

Features

- Internal Shunt Resistor
- Integrated Gate Drivers and Bootstrap Diodes
- Temperature Monitor
- Fully Isolated Package
- Low $V_{CE(on)}$ Non Punch Through IGBT Technology
- Undervoltage lockout for all channels
- Matched propagation delay for all channels
- Schmitt-triggered input logic
- Cross-conduction prevention logic
- Lower di/dt gate driver for better noise immunity
- Motor Power range 0.4~0.75kW / 85~253 Vac
- Isolation 2000V_{RMS}/1min



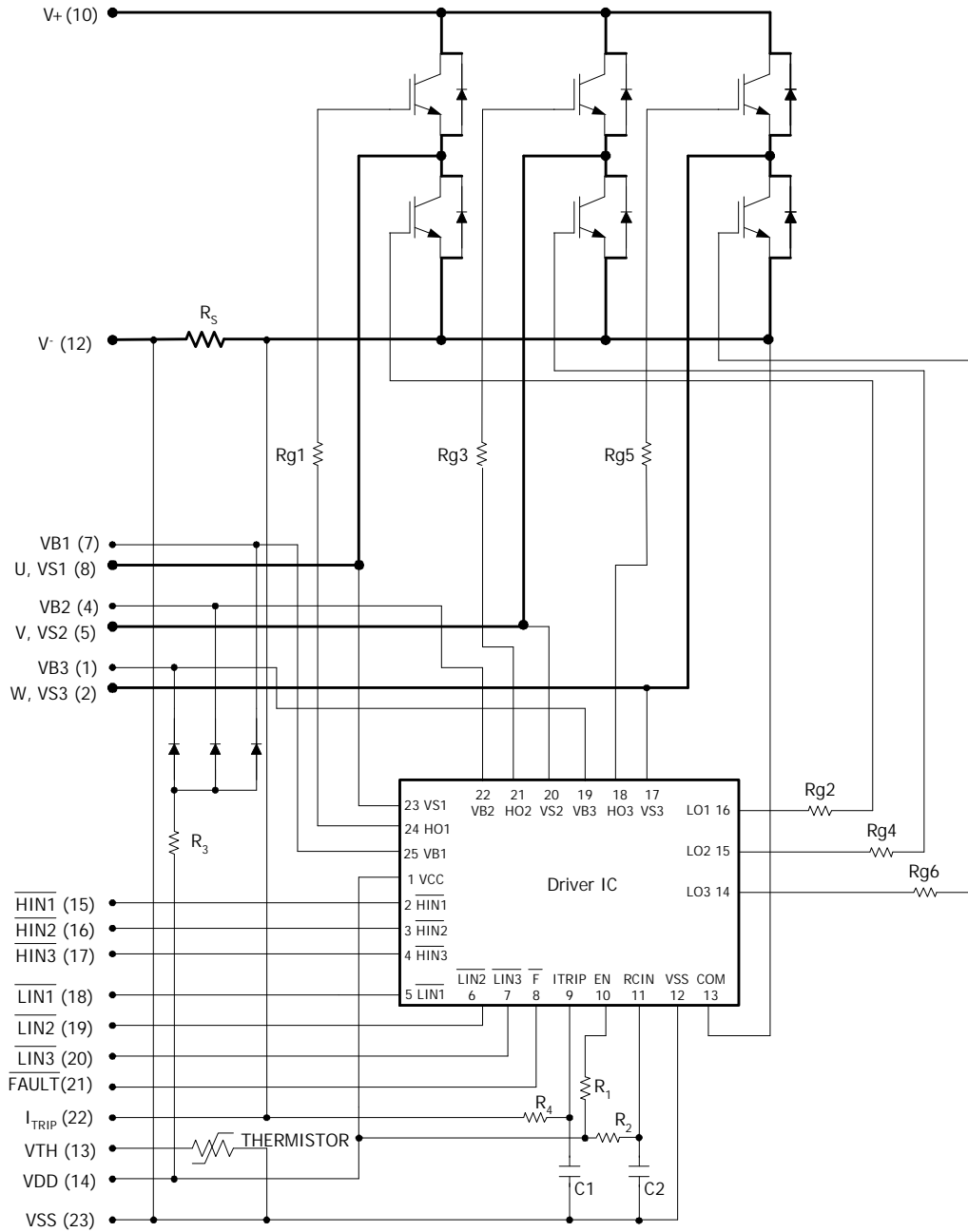
Absolute Maximum Ratings

| Parameter | Description | Max. Value | Units |
|-------------------------|---------------------------------------|-------------|------------------|
| V_{CES} | Maximum IGBT Blocking Voltage | 600 | V |
| V^+ | Positive Bus Input Voltage | 450 | |
| $I_o @ T_c=25^\circ C$ | RMS Phase Current (see Note 1) | 10 | A |
| $I_o @ T_c=100^\circ C$ | RMS Phase Current (see Note 1) | 5 | |
| I_{pk} | Maximum Peak Phase Current (tp<100ms) | 15 | |
| F_p | Maximum PWM Carrier Frequency | 20 | kHz |
| P_d | Maximum Power dissipation per Phase | 20 | W |
| V_{iso} | Isolation Voltage (1min) | 2000 | V _{RMS} |
| T_J (IGBT & Diodes) | Operating Junction temperature Range | -40 to +150 | °C |
| T_J (Driver IC) | Operating Junction temperature Range | -40 to +150 | |
| T | Mounting torque Range (M3 screw) | 0.8 to 1.0 | Nm |

Note 1: Limited by current protection, see table "Inverter Section Electrical Characteristics" on page 3

IRAMS10UP60B

Internal Electrical Schematic - IRAMS10UP60B



Inverter Section Electrical Characteristics @ T_J=25°C

| Symbol | Parameter | Min | Typ | Max | Units | Conditions |
|----------------------------|--|------|------|------|-------|--|
| V _{(BR)CES} | Collector-to-Emitter Breakdown Voltage | 600 | --- | --- | V | V _{IN} =5V, I _C =250μA |
| ΔV _{(BR)CES} / ΔT | Temperature Coeff. Of Breakdown Voltage | --- | 0.57 | --- | V/°C | V _{IN} =5V, I _C =1.0mA (25°C - 150°C) |
| V _{CE(ON)} | Collector-to-Emitter Saturation Voltage | --- | 1.7 | 2.0 | V | I _C =5A T _J =25°C, V _{DD} =15V |
| | | --- | 2.0 | 2.4 | | I _C =5A T _J =150°C |
| I _{CES} | Zero Gate Voltage Collector Current-to-Emitter | --- | 5 | 15 | μA | V _{IN} =5V, V ⁺ =600V |
| | | --- | 10 | 40 | | V _{IN} =5V, V ⁺ =600V, T _J =150°C |
| I _{Ik_module} | Zero Gate Voltage Phase-to-phase Current | -- | -- | 50 | μA | V _{IN} =5V, V ⁺ =600V |
| V _{FM} | Diode Forward Voltage Drop | --- | 1.8 | 2.35 | V | I _C =5A |
| | | --- | 1.3 | 1.7 | | I _C =5A, T _J =150°C |
| I _{BUS_Trip} | Current Protection Threshold (positive going) | 13.1 | | 16.4 | A | T _J =-40°C to 150°C |

Inverter Section Switching Characteristics @ T_J=25°C

| Symbol | Parameter | Min | Typ | Max | Units | Conditions |
|------------------|-----------------------------------|-------------|-----|-----|-------|---|
| E _{on} | Turn-On Switching Loss | --- | 200 | 235 | μJ | I _C =5A, V ⁺ =400V V _{DD} =15V, L=1mH T _J =25°C |
| E _{off} | Turn-Off Switching Loss | --- | 75 | 100 | | |
| E _{tot} | Total Switching Loss | --- | 275 | 335 | | |
| E _{on} | Turn-on Switching Loss | --- | 300 | 360 | μJ | See CT1 T _J =150°C Energy losses include "tail" and diode reverse recovery |
| E _{off} | Turn-off Switching Loss | --- | 135 | 165 | | |
| E _{tot} | Total Switching Loss | --- | 435 | 525 | | |
| E _{rec} | Diode Rev. Recovery energy | --- | 30 | 40 | μJ | T _J =150°C, V ⁺ =400V V _{DD} =15V, |
| t _{rr} | Diode Reverse Recovery time | --- | 100 | 145 | ns | I _F =5A, L=1mH |
| RBSOA | Reverse Bias Safe Operating Area | FULL SQUARE | | | | T _J =150°C, I _C =5A, V _P =600V V ⁺ =480V, V _{DD} =+15V to 0V See CT3 |
| SCSOA | Short Circuit Safe Operating Area | 10 | --- | --- | μs | T _J =150°C, V _P =600V, V ⁺ =360V, V _{DD} =+15V to 0V See CT2 |

Thermal Resistance

| Symbol | Parameter | Min | Typ | Max | Units | Conditions |
|----------------------|---|-----|-----|-----|-------|--|
| R _{th(J-C)} | Junction to case thermal resistance, each IGBT under inverter operation. | --- | 4.2 | 4.7 | °C/W | Flat, greased surface. Heatsink compound thermal conductivity - 1W/mK |
| R _{th(J-C)} | Junction to case thermal resistance, each Diode under inverter operation. | --- | 5.5 | 6.5 | °C/W | |
| R _{th(C-S)} | Case to Sink thermal resistance | --- | 0.1 | --- | °C/W | |

Absolute Maximum Ratings Driver Function

Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to V_{SS} . (Note 2)

| Symbol | Definition | Min | Max | Units |
|--------------|---|------|-----------------------------|-------|
| $V_{S1,2,3}$ | High Side offset voltage | -0.3 | 600 | V |
| $V_{B1,2,3}$ | High Side floating supply voltage | -0.3 | 20 | V |
| V_{DD} | Low Side and logic fixed supply voltage | -0.3 | 20 | V |
| V_{IN} | Input voltage LIN, HIN, T/I _{TRIP} | -0.3 | $V_{SS}+15$ or $V_{CC}+0.3$ | V |
| T_J | Junction Temperature | -40 | 150 | °C |

Raccomended Operating Conditions Driver Function

The Input/Output logic timing diagram is shown in Figure 1. For proper operation the device should be used within the recommended conditions. All voltages are absolute referenced to V_{SS} . The V_S offset is tested with all supplies biased at 15V differential (Note 2). All input pin (V_{IN}) and I_{TRIP} are clamped with a 5.2V zener diode and pull-up resistor to V_{DD}

| Symbol | Definition | Min | Max | Units |
|--------------|--|----------|------------|-------|
| $V_{B1,2,3}$ | High side floating supply voltage | V_S+12 | V_S+20 | V |
| $V_{S1,2,3}$ | High side floating supply offset voltage | Note 3 | 600 | |
| V_{DD} | Low side and logic fixed supply voltage | 12 | 20 | V |
| V_{IN} | Logic input voltage LIN, HIN | V_{SS} | $V_{SS}+5$ | V |

Static Electrical Characteristics Driver Function

V_{BIAS} (V_{DD} , $V_{BS1,2,3}$)=15V, unless otherwise specified. The V_{IN} and I_{IN} parameters are referenced to V_{SS} and are applicable to all six channels. (Note 2)

| Symbol | Definition | Min | Typ | Max | Units |
|----------------------------|---|------|------|------|-------|
| $V_{IN,th+}$ | Positive going input threshold | 3.0 | --- | --- | V |
| $V_{IN,th-}$ | Negative going input threshold | --- | --- | 0.8 | V |
| V_{CCUV+} V_{BSUV+} | V_{CC} and V_{BS} supply undervoltage Positive going threshold | 10.6 | 11.1 | 11.6 | V |
| V_{CCUV-} V_{BSUV-} | V_{CC} and V_{BS} supply undervoltage Negative going threshold | 10.4 | 10.9 | 11.4 | V |
| V_{CCUVH} V_{BSUVH} | V_{CC} and V_{BS} supply undervoltage $I_{lockout}$ hysteresis | --- | 0.2 | --- | V |
| I_{OBS} | Quiescent V_{BS} supply current | --- | 70 | 120 | μA |
| I_{OCC} | Quiescent V_{CC} supply current | --- | 1.6 | 2.3 | mA |
| I_{LK} | Offset Supply Leakage Current | --- | --- | 50 | μA |
| I_{IN+} | Input bias current (OUT=LO) | --- | 100 | 220 | μA |
| I_{IN+} | Input bias current (OUT=HI) | --- | 200 | 300 | μA |
| $V(I_{TRIP})$ | I_{TRIP} threshold Voltage (OUT=HI or OUT=LO) | 0.44 | 0.49 | 0.54 | V |

Dynamic Electrical Characteristics

$V_{DD}=V_{BS}=V_{BIAS}=15V$, $PWM_{IN}=2kHz$, $V_{IN_ON}=V_{IN_th+}$, $V_{IN_OFF}=V_{IN_th-}$
 $T_A=25^{\circ}C$, unless otherwise specified

| Symbol | Definition | Min | Typ | Max | Units |
|--------------|---|-----|-----|-----|-------|
| T_{ON} | Input to output propagation turn-on delay time (see fig.11) | - | 470 | - | ns |
| T_{OFF} | Input to output propagation turn-off delay time (see fig. 11) | - | 615 | - | ns |
| D_T | Dead Time | - | 290 | - | ns |
| I/T_{Trip} | T/I_{Trip} to six switch to turn-off propagation delay (see fig. 2) | - | 750 | - | ns |
| T_{FCTRL} | Post I_{Trip} to six switch to turn-off clear time (see fig. 2) | - | 9 | - | ms |

Internal NTC - Thermistor Characteristics

| Parameter | Typ | Units | Conditions |
|-----------------------------------|-------------------|-----------------|------------------------------------|
| R_{25} Resistance | 100 +/- 3% | k Ω | $T_C = 25^{\circ}C$ |
| R_{125} Resistance | 2.522 \pm 10.9% | k Ω | $T_C = 125^{\circ}C$ |
| B B-constant (25-50 $^{\circ}C$) | 4250 +/- 2% | k | $R_2 = R_1 e^{[B(1/T_2 - 1/T_1)]}$ |
| Temperature Range | -40 / 125 | $^{\circ}C$ | |
| Typ. Dissipation constant | 1 | mW/ $^{\circ}C$ | $T_C = 25^{\circ}C$ |

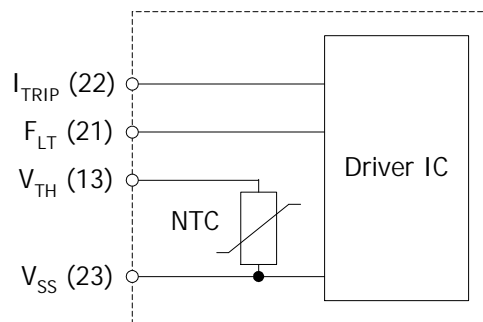
Internal Current Sensing Resistor - Shunt Characteristics

| Parameter | | Units |
|-----------------------|---------------|-------------|
| Resistance | 33.3 \pm 1% | m Ω |
| Tolerance | \pm 1% | |
| Max Power Dissipation | 2.2 | W |
| Temperature Range | -40 / 125 | $^{\circ}C$ |

Note 2: For more details, see IR21363 data sheet

Note 3: Logic operational for V_S from $V^- -5V$ to $V^+ +600V$. Logic state held for V_S from $V^- -5V$ to $V^- -V_{BS}$. (please refer to DT97-3 for more details)

Thermistor Built-in IRAMS10UP60B



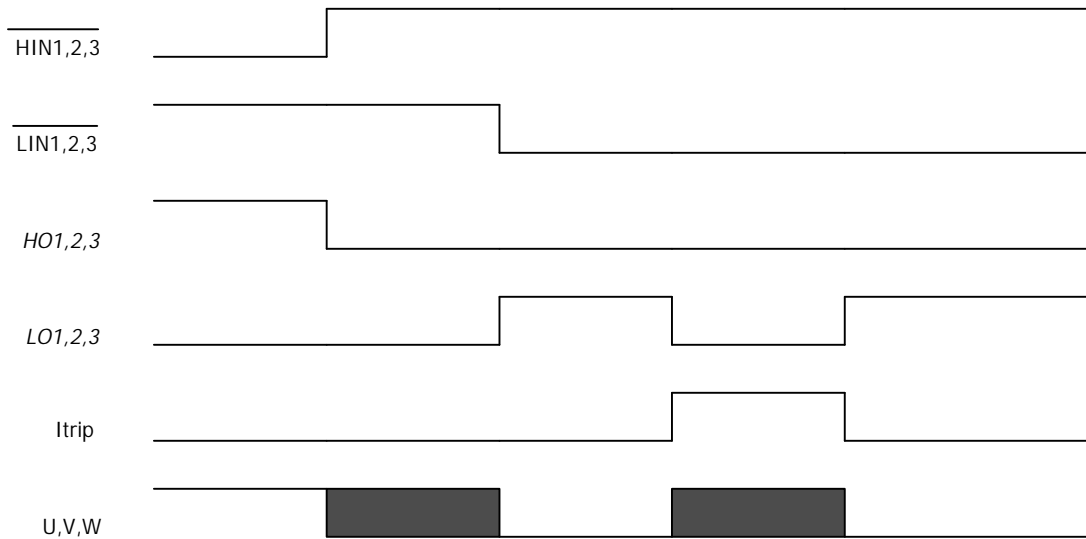
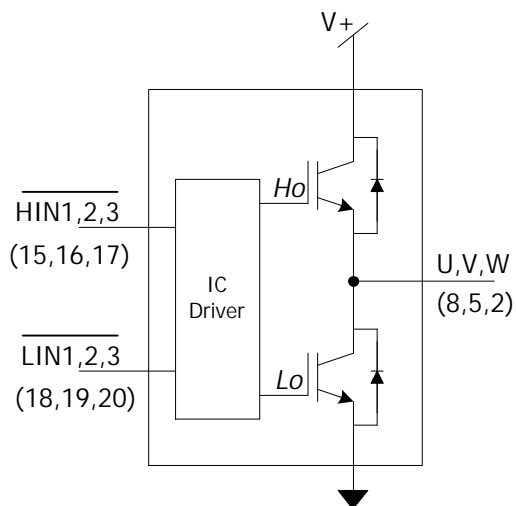
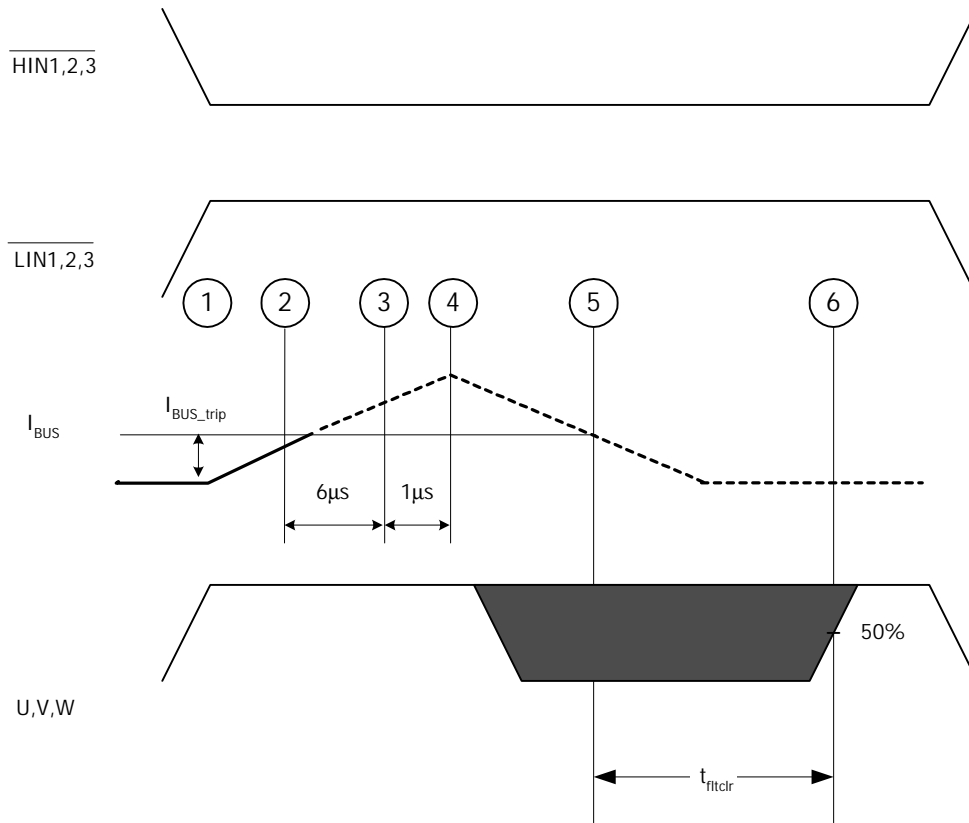


Figure1. Input/Output Timing Diagram

Note 4: The shaded area indicates that both high-side and low-side switches are off and therefore the half-bridge output voltage would be determined by the direction of current flow in the load.



| I_{trip} | $\overline{HIN1,2,3}$ | $\overline{LIN1,2,3}$ | U,V,W |
|------------|-----------------------|-----------------------|---------|
| 0 | 0 | 1 | $V+$ |
| 0 | 1 | 0 | 0 |
| 0 | 1 | 1 | X |
| 1 | X | X | X |



Sequence of events:

- 1-2) Current begins to rise
- 2) Current reaches I_{BUS_Trip} level
- 2-3) Current is higher than I_{BUS_Trip} for at least 6µs. This value is the worst-case condition with very low over-current. In case of high current (short circuit), the actual delay will be smaller.
- 3-4) Delay between driver identification of over-current condition and disabling of all outputs
- 4) Current starts decreasing, eventually reaching 0
- 5) Current goes below I_{BUS_Trip} , the driver starts its auto-reset sequence
- 6) Driver is automatically reset and normal operation can resume (over-current condition must be removed by the time the drivers automatically resets itself)

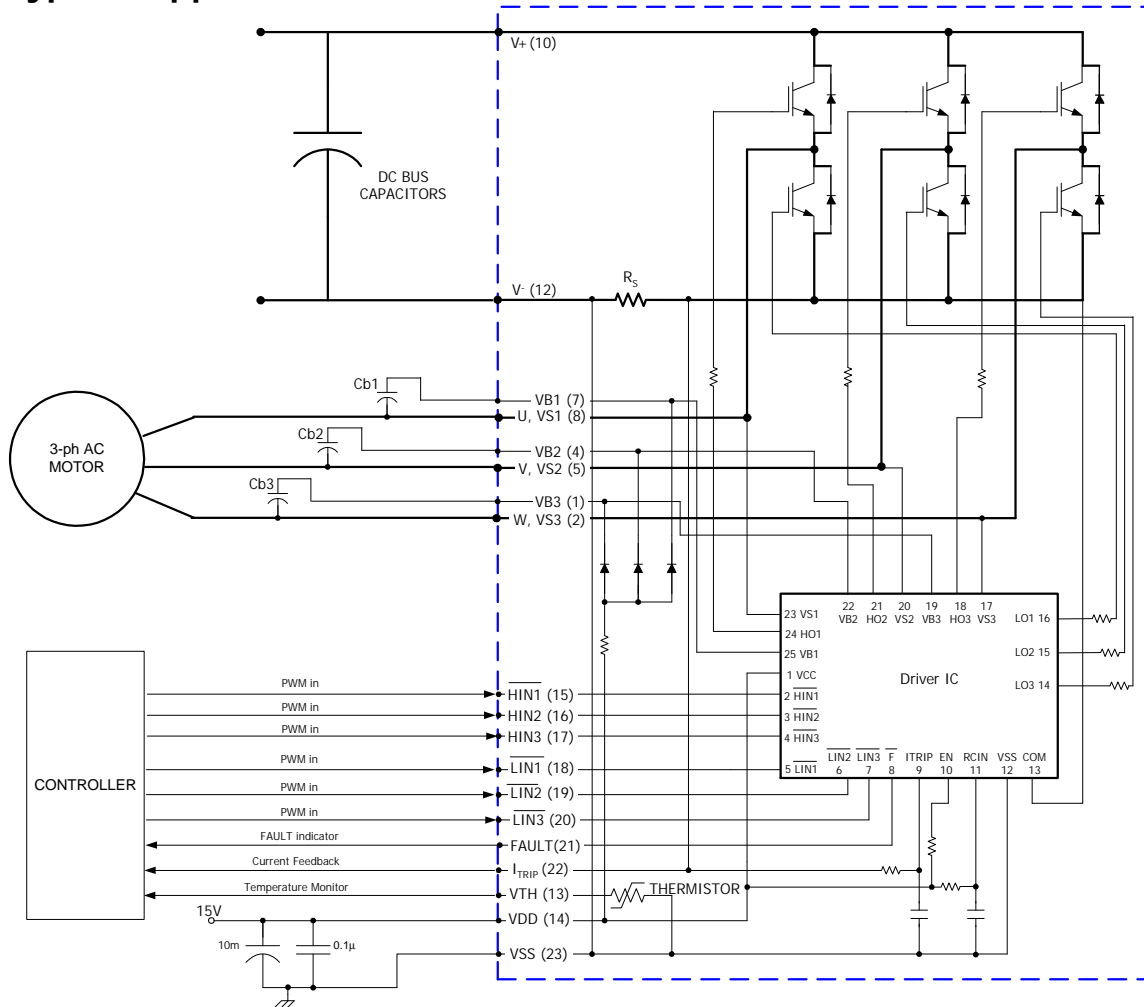
Figure 2. I_{Trip} Timing Waveform

Note 5: The shaded area indicates that both high-side and low-side switches are off and therefore the half-bridge output voltage would be determined by the direction of current flow in the load.

Module Pin-Out Description

| Pin | Name | Description |
|-----|--------|---|
| 1 | VB3 | High Side Floating Supply Voltage 3 |
| 2 | W, VS3 | Output 3 - High Side Floating Supply Offset Voltage |
| 3 | na | none |
| 4 | VB2 | High Side Floating Supply voltage 2 |
| 5 | V, VS2 | Output 2 - High Side Floating Supply Offset Voltage |
| 6 | na | none |
| 7 | VB1 | High Side Floating Supply voltage 1 |
| 8 | U, VS1 | Output 1 - High Side Floating Supply Offset Voltage |
| 9 | na | none |
| 10 | V+ | Positive Bus Input Voltage |
| 11 | na | none |
| 12 | V- | Negative Bus Input Voltage |
| 13 | VTH | Temperature Feedback |
| 14 | VDD | +15V Main Supply |
| 15 | HIN1 | Logic Input High Side Gate Driver - Phase 1 |
| 16 | HIN2 | Logic Input High Side Gate Driver - Phase 2 |
| 17 | HIN3 | Logic Input High Side Gate Driver - Phase 3 |
| 18 | LIN1 | Logic Input Low Side Gate Driver - Phase 1 |
| 19 | LIN2 | Logic Input Low Side Gate Driver - Phase 2 |
| 20 | LIN3 | Logic Input Low Side Gate Driver - Phase 3 |
| 21 | FAULT | Fault indicator |
| 22 | Itrip | Current Sense and Itrip Pin |
| 23 | VSS | Negative Main Supply |

Typical Application Connection IRAMS10UP60B



1. Electrolytic bus capacitors should be mounted as close to the module bus terminals as possible to reduce ringing and EMI problems. Additional high frequency ceramic capacitor mounted close to the module pins will further improve performance.
2. In order to provide good decoupling between V_{CC} -Gnd and V_B - V_{SS} terminals, the capacitors shown connected between these terminals should be located very close to the module pins. Additional high frequency capacitors, typically 0.1mF, are strongly recommended.
3. Value of the boot-strap capacitors depends upon the switching frequency. Their selection should be made based on IR design tip DN 98-2a, application note AN-1044 or Figure 9.
4. Current sense signal can be obtained from pin 22 and pin 23
5. After approx. 8 ms the FAULT is reset
6. PWM generator must be disabled within Fault duration to guarantee shutdown of the system, overcurrent condition must be cleared before resuming operation

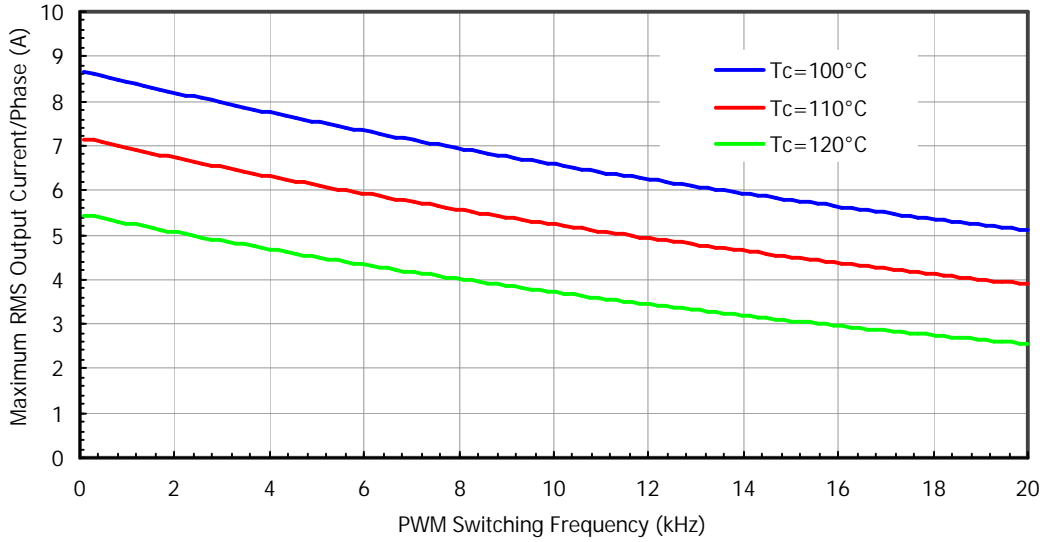


Figure 3. Maximum sinusoidal phase current as function of switching frequency
 $V^+=400V$, $T_J=150^\circ C$, Modulation Depth=0.8, PF=0.6

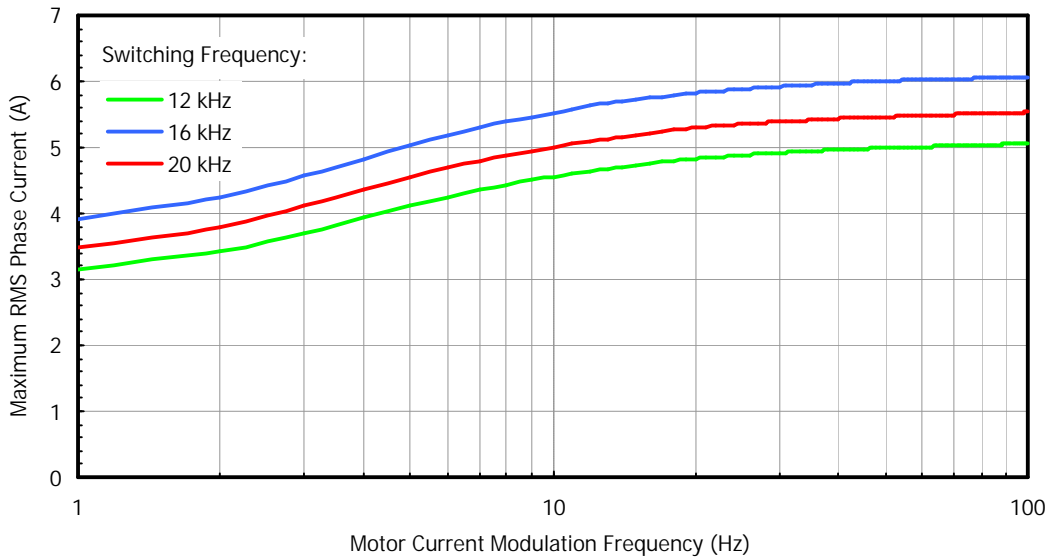


Figure 4. Maximum sinusoidal phase current as function of modulation frequency
 $V^+=400V$, $T_J=150^\circ C$, $T_c=100^\circ C$, Modulation Depth=0.8, PF=0.6

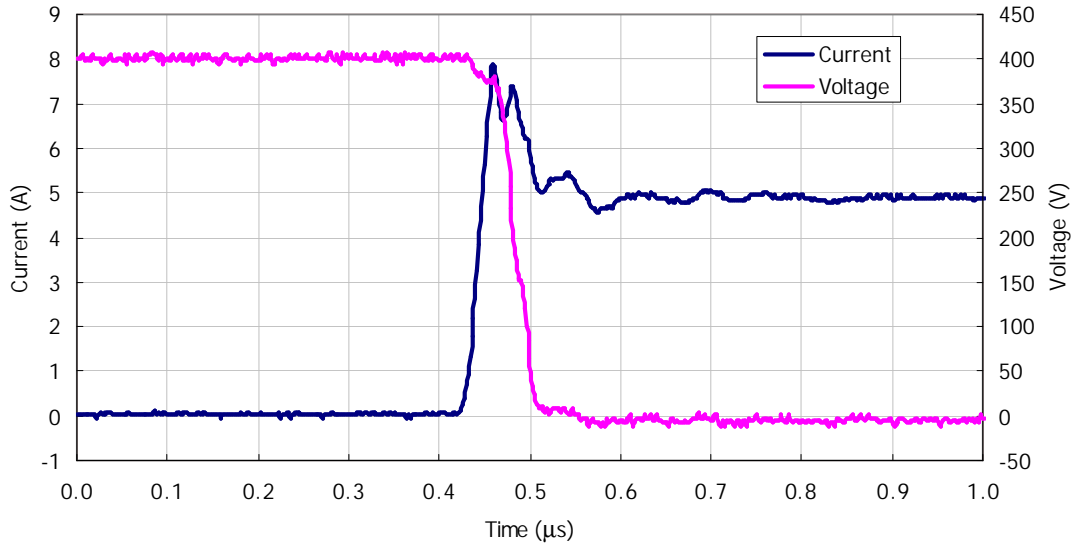


Figure 5. IGBT Turn-on. Typical turn-on waveform @ $T_J=150^{\circ}\text{C}$, $V^+=400\text{V}$

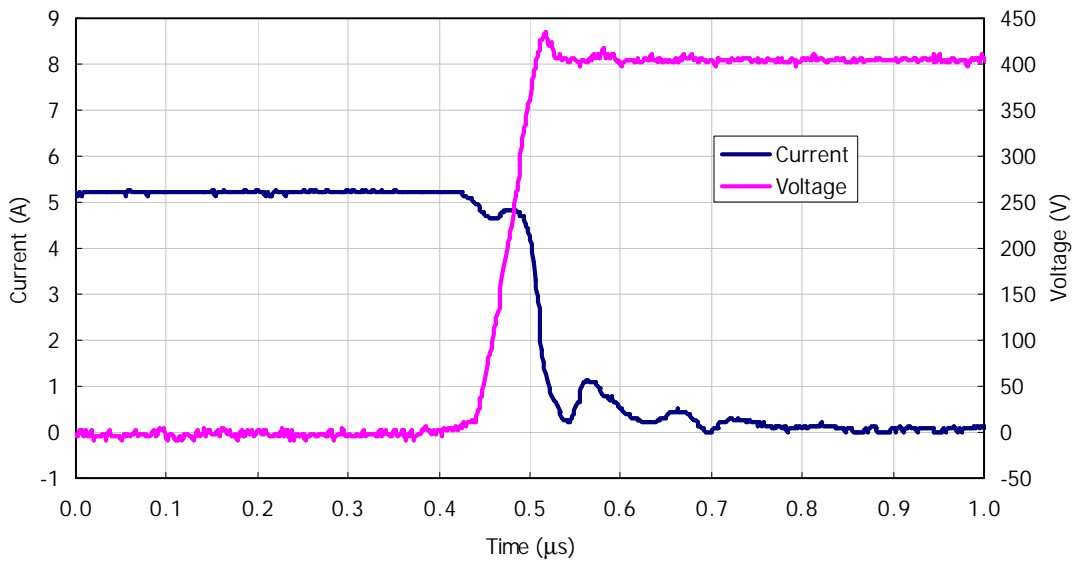


Figure 6. IGBT Turn-off. Typical turn-off waveform @ $T_J=150^{\circ}\text{C}$, $V^+=400\text{V}$

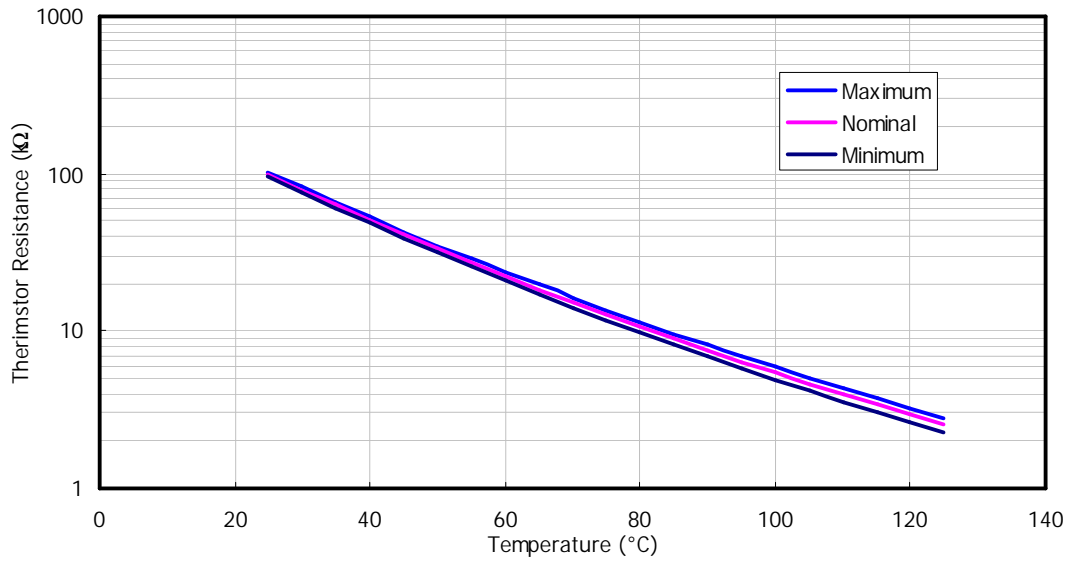


Figure 7. Variation of thermistor resistance with temperature

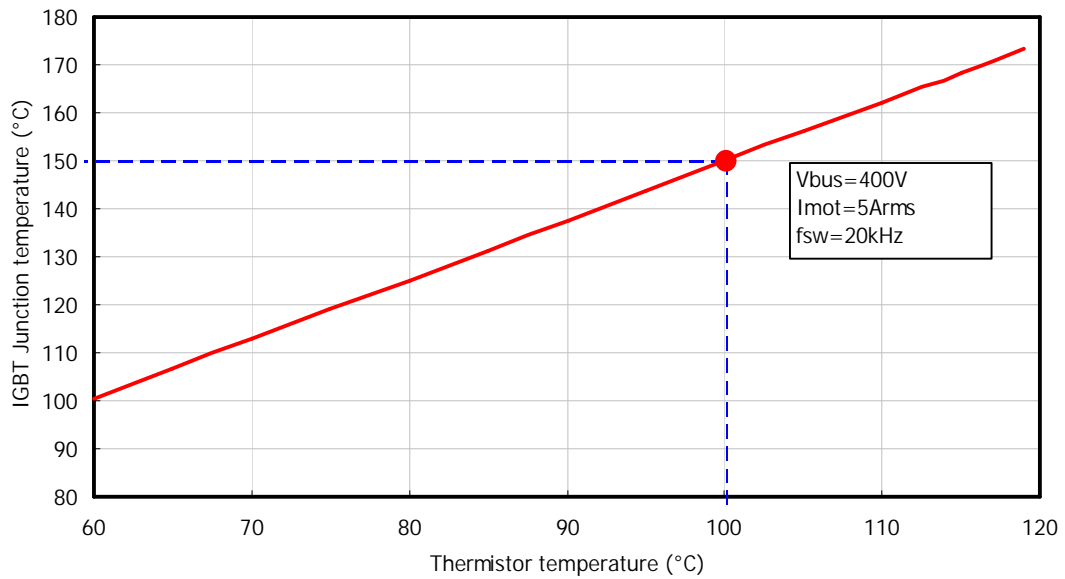


Figure 8. Estimated maximum IGBT junction temperature with thermistor temperature

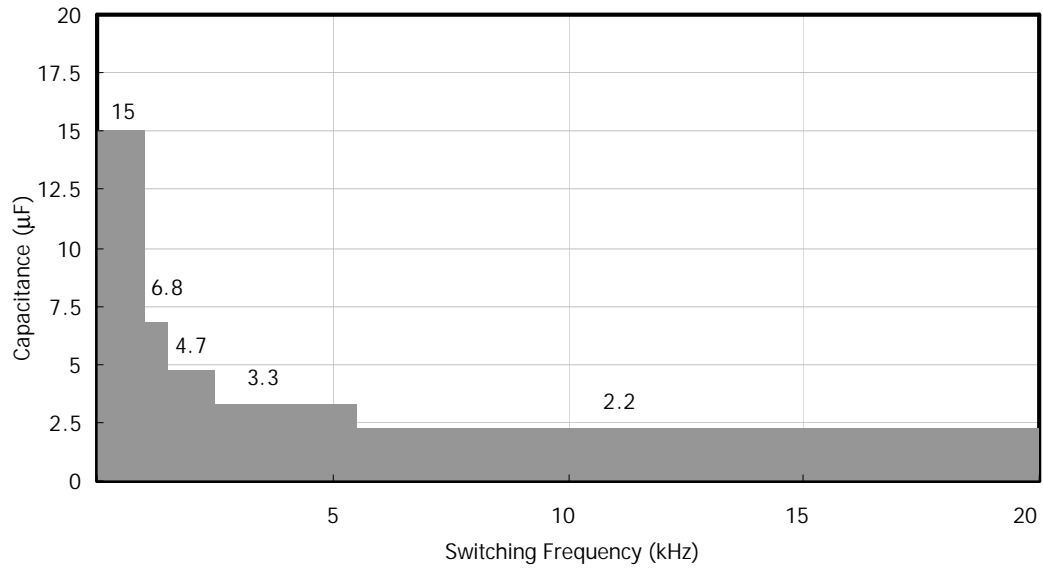


Figure 9. Recommended minimum Bootstrap Capacitor Value Vs Switching Frequency

Figure 11. Switching Parameter Definitions

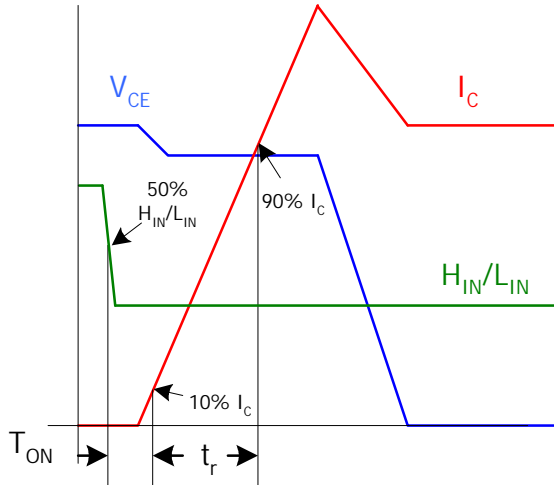


Figure 11a. Input to Output propagation turn-on delay time

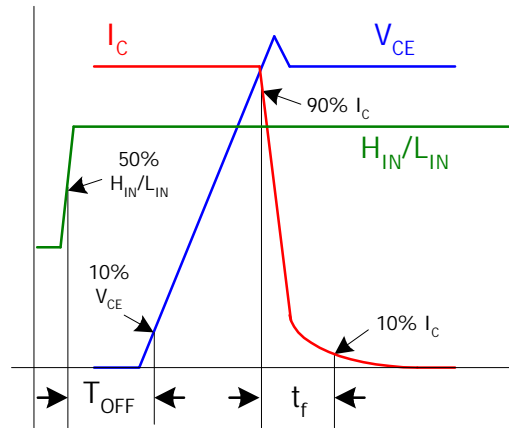


Figure 11b. Input to Output propagation turn-off delay time

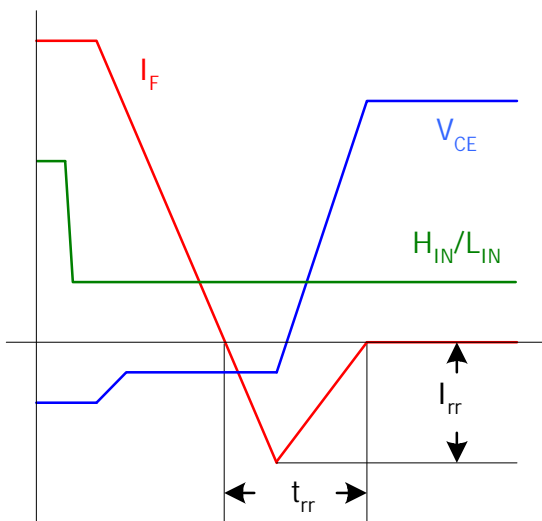


Figure 11c. Diode Reverse Recovery

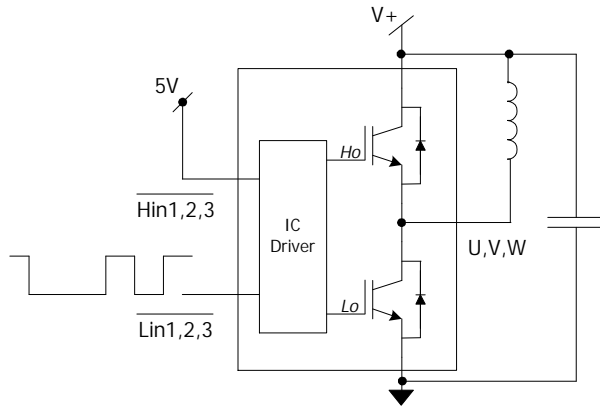


Figure CT1. Switching Loss Circuit

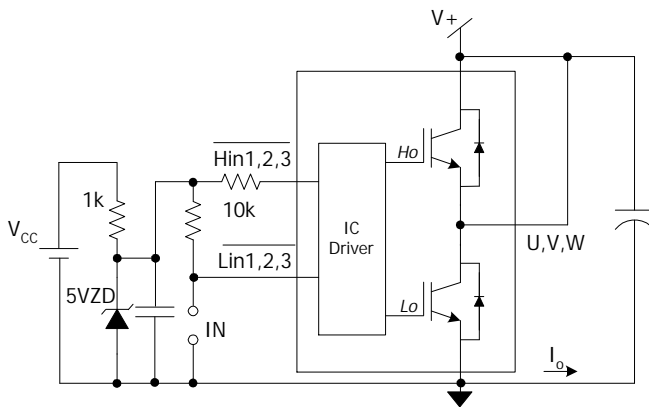
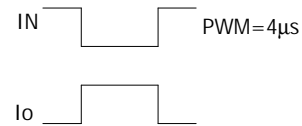


Figure CT2. S.C.SOA Circuit



V_P =Peak Voltage on the IGBT die

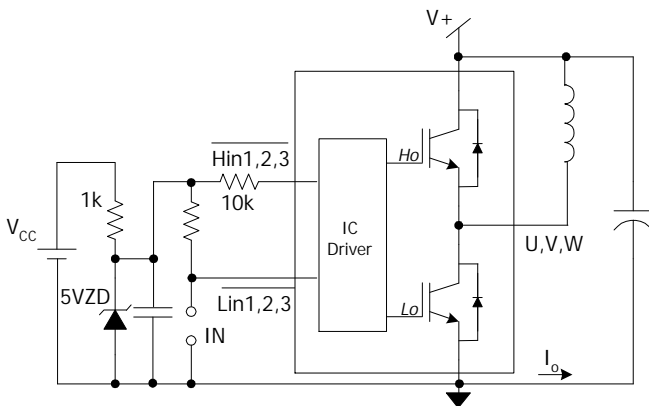
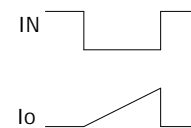


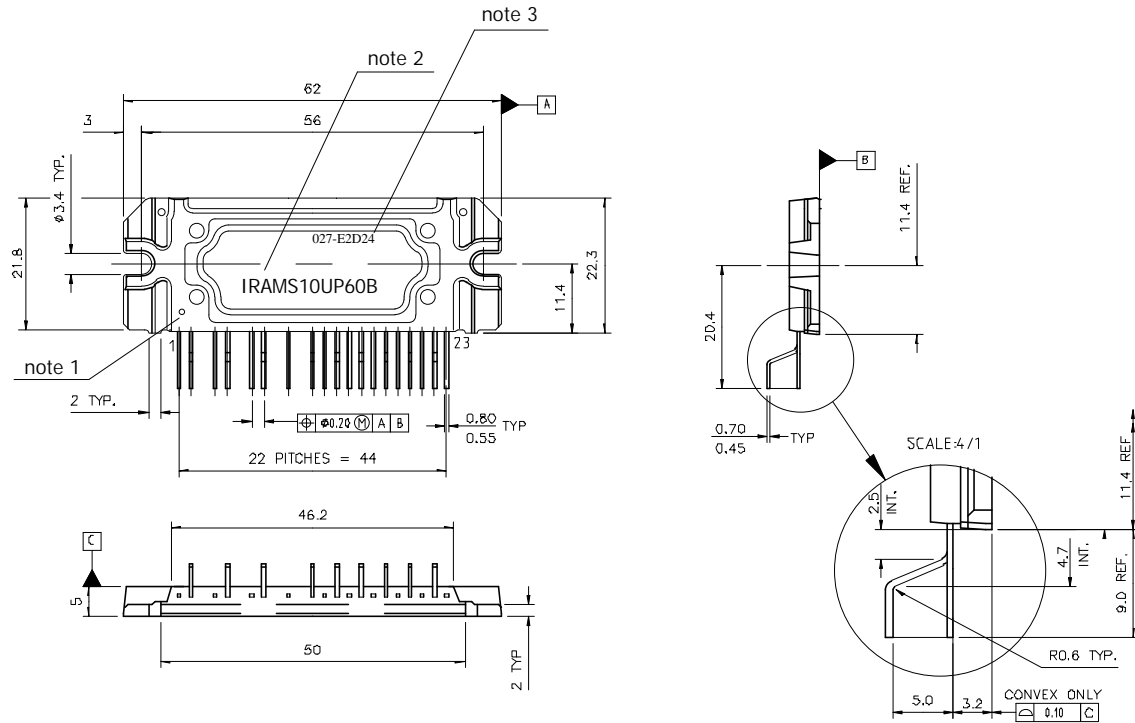
Figure CT3. R.B.SOA Circuit



V_P =Peak Voltage on the IGBT die

IRAMS10UP60B

Package Outline



Standard pin leadforming option

Notes:

Dimensions in mm

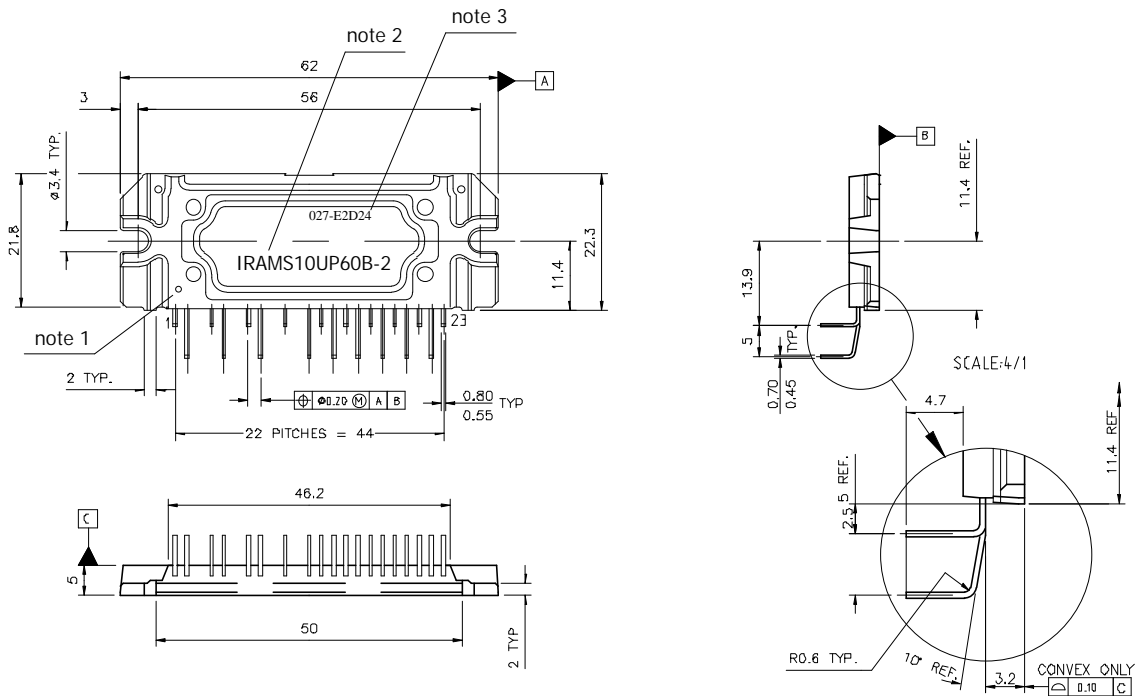
1- Marking for pin 1 identification

2- Product Part Number

3- Lot and Date code marking

For mounting instruction, see AN1049

Package Outline



Pin leadforming option -2

Notes:

Dimensions in mm

- 1- Marking for pin 1 identification
- 2- Product Part Number
- 3- Lot and Date code marking

Data and Specifications are subject to change without notice

